

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π-MOSVI)

2SK3667

Switching Regulator Applications

- Low drain-source ON-resistance: $R_{DS(ON)} = 0.75\ \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 5.5\ S$ (typ.)
- Low leakage current: $I_{DSS} = 100\ \mu A$ (max) ($V_{DS} = 600\ V$)
- Enhancement mode: $V_{th} = 2.0\ to\ 4.0\ V$ ($V_{DS} = 10\ V$, $I_D = 1\ mA$)

Absolute Maximum Ratings (Ta = 25°C)

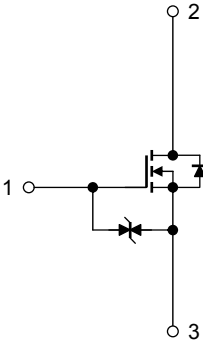
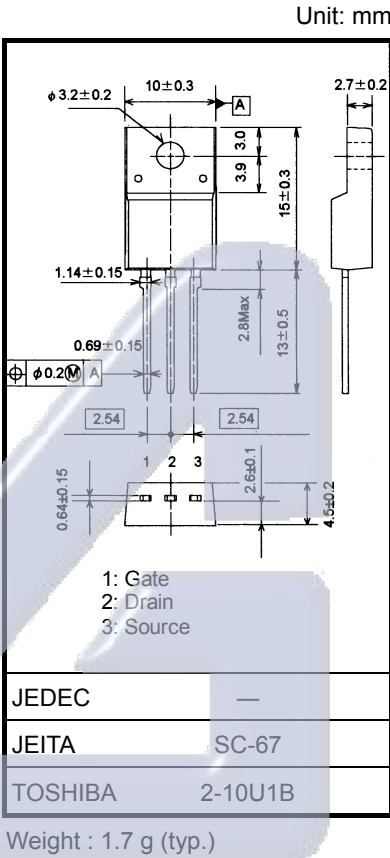
Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	600	V
Drain-gate voltage ($R_{GS} = 20\ k\Omega$)		V_{DGR}	600	V
Gate-source voltage		V_{GSS}	± 30	V
Drain current	DC (Note 1)	I_D	7.5	A
	Pulse ($t = 1\ ms$) (Note 1)	I_{DP}	30	
Drain power dissipation ($T_c = 25^\circ C$)		P_D	45	W
Single pulse avalanche energy (Note 2)		E_{AS}	189	mJ
Avalanche current		I_{AR}	7.5	A
Repetitive avalanche energy (Note 3)		E_{AR}	4.5	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

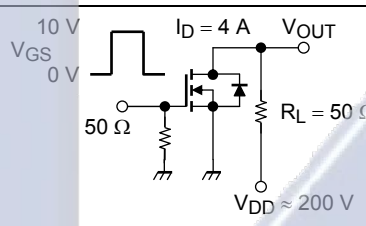
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	2.78	°C/W
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	°C/W

- Note 1: Ensure that the channel temperature does not exceed 150°C.
- Note 2: $V_{DD} = 90\ V$, $T_{ch} = 25^\circ C$, $L = 5.88\ mH$, $I_{AR} = 7.5\ A$, $R_G = 25\ \Omega$
- Note 3: Repetitive rating: pulse width limited by maximum channel temperature
- This transistor is an electrostatic-sensitive device. Please handle with caution.

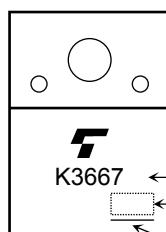


Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Gate-source breakdown voltage		$V_{(BR)GSS}$	$I_G = \pm 10 \mu\text{A}, V_{DS} = 0 \text{ V}$	± 30	—	—	V
Drain cut-off current		I_{DSS}	$V_{DS} = 600 \text{ V}, V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$	2.0	—	4.0	V
Drain-source ON-resistance		$R_{DS(ON)}$	$V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$	—	0.75	1.0	Ω
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}, I_D = 4 \text{ A}$	1.5	5.5	—	S
Input capacitance		C_{iss}	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	—	1300	—	pF
Reverse transfer capacitance		C_{rss}		—	12	—	
Output capacitance		C_{oss}		—	120	—	
Switching time	Rise time	t_r		—	20	—	ns
	Turn-on time	t_{on}		—	50	—	
	Fall time	t_f		—	35	—	
	Turn-off time	t_{off}		—	150	—	
Total gate charge		Q_g	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$	—	33	—	nC
Gate-source charge		Q_{gs}		—	18	—	
Gate-drain charge		Q_{gd}		—	15	—	

Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	7.5	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	30	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 7.5 \text{ A}, V_{GS} = 0 \text{ V}$	—	—	1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 7.5 \text{ A}, V_{GS} = 0 \text{ V},$	—	1200	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	12	—	μC

Marking

Part No. (or abbreviation code)

Lot No.
(weekly code)

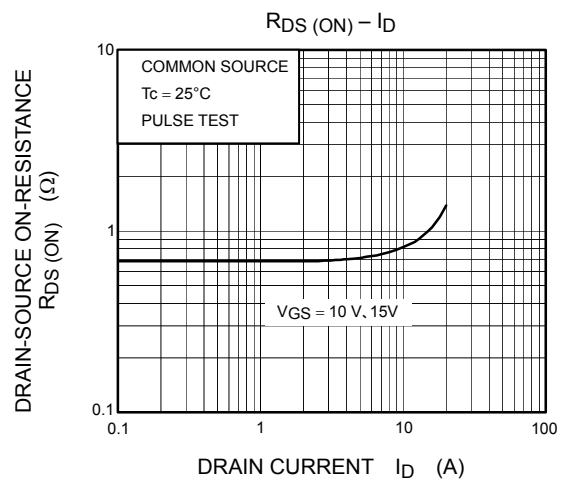
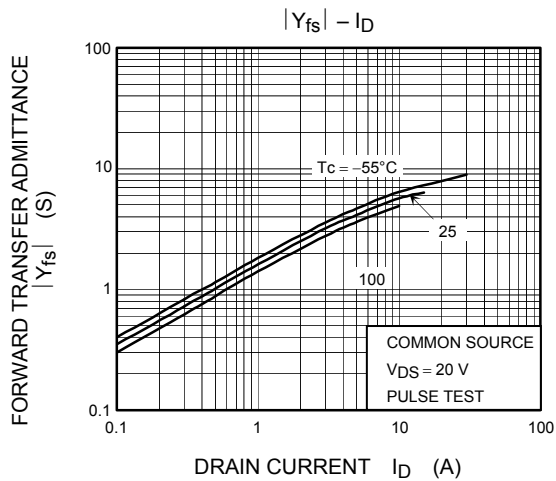
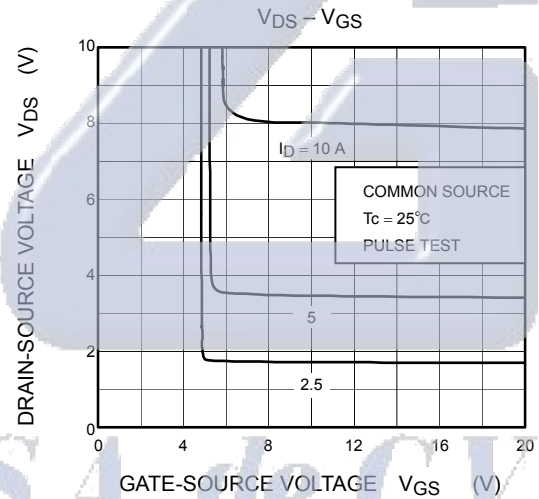
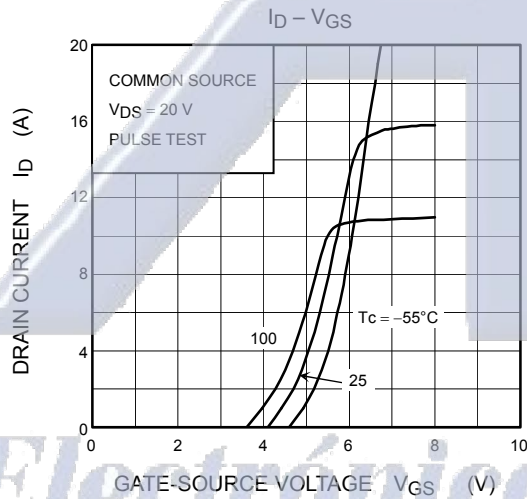
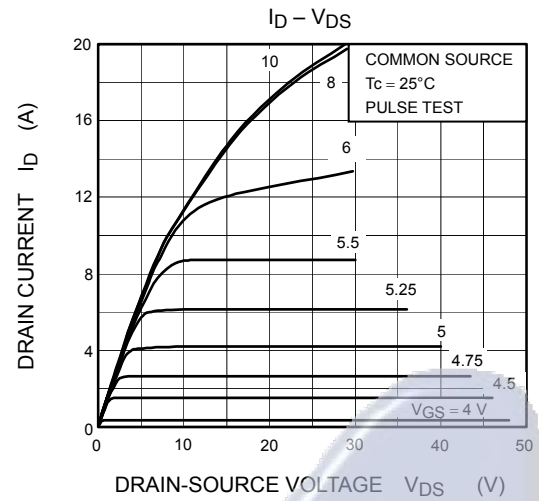
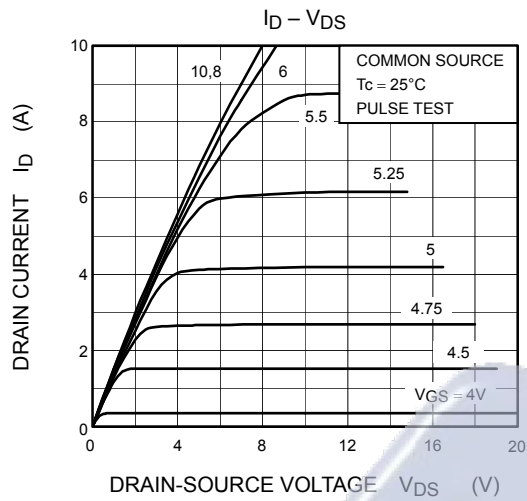
Note 4

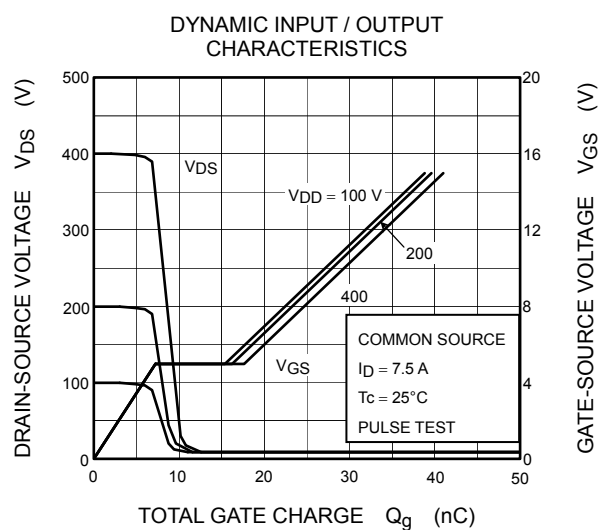
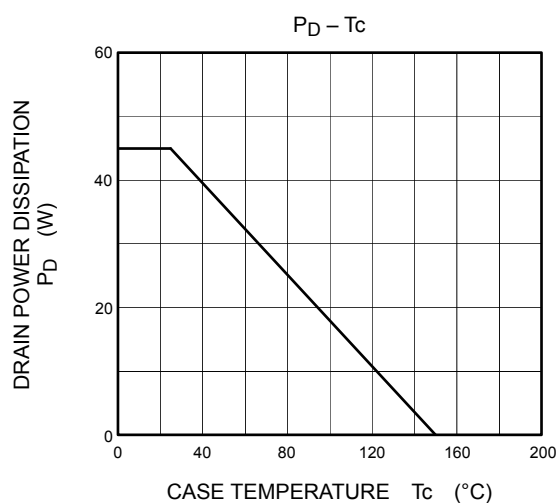
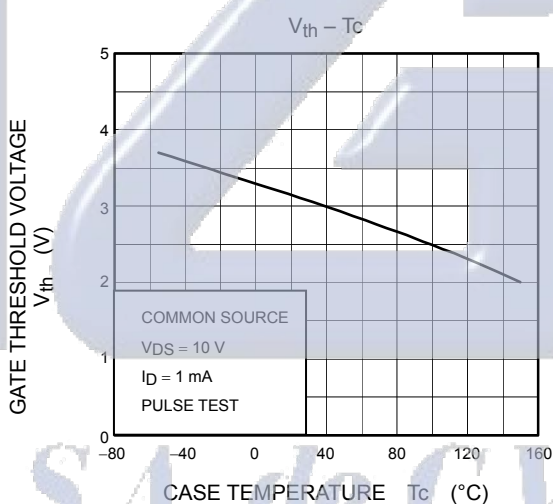
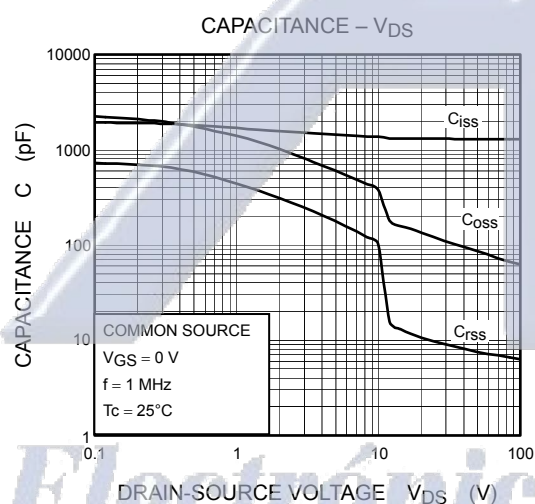
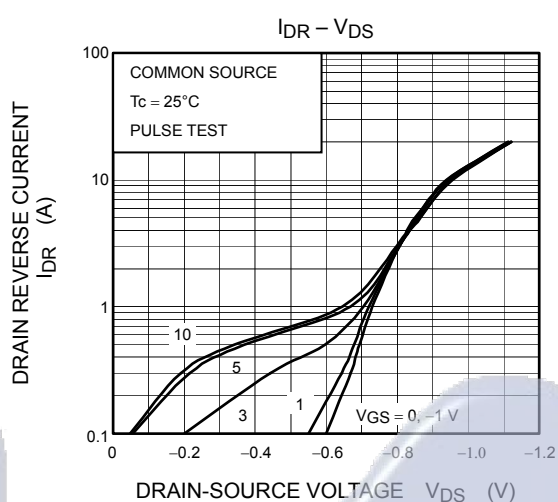
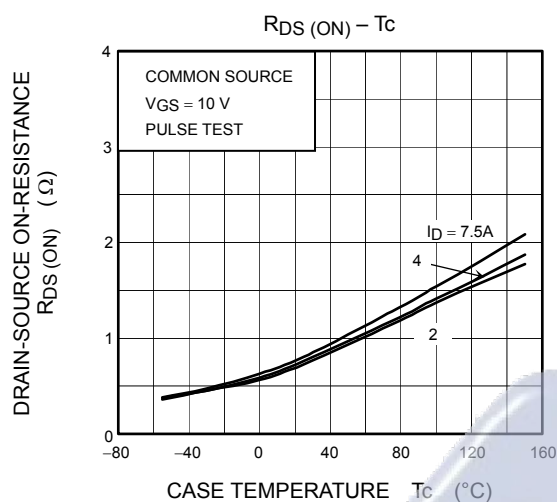
Note 4: A line under a Lot No. identifies the indication of product Labels.

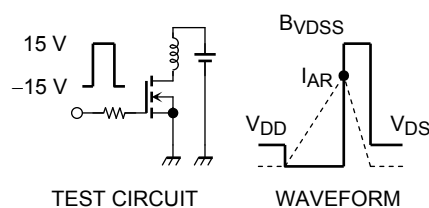
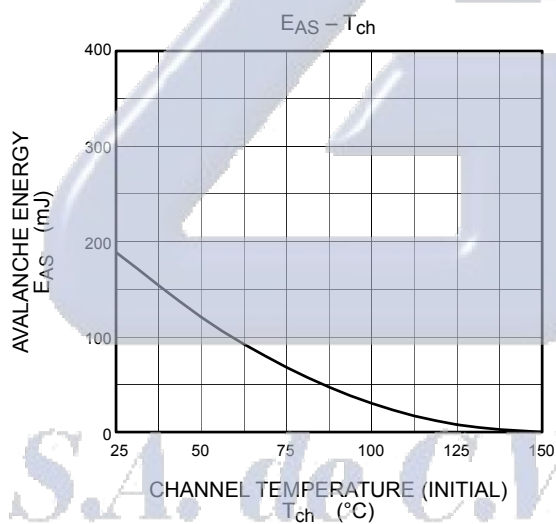
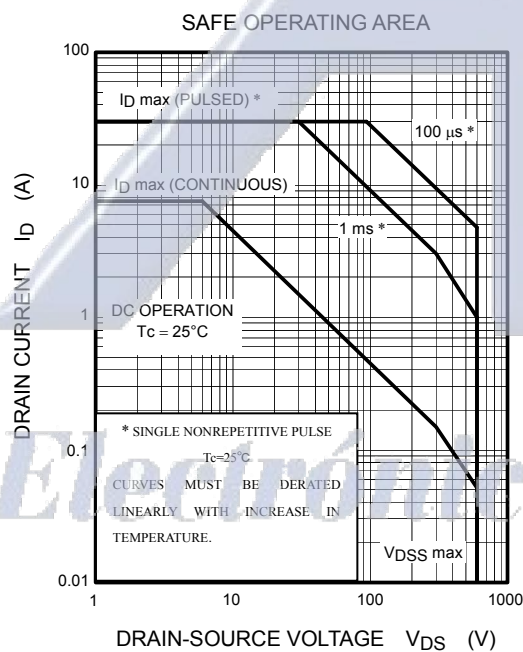
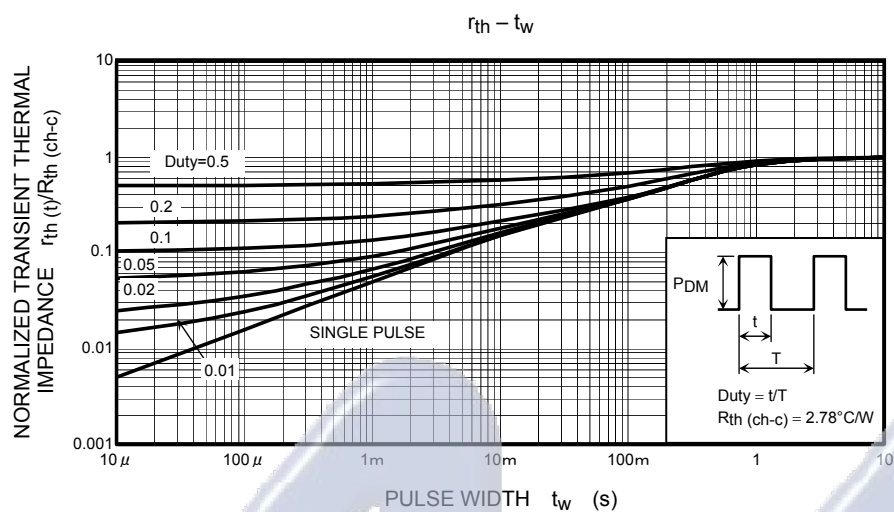
Not underlined: $[[Pb]]/INCLUDES > MCV$

Underlined: $[[G]]/RoHS \text{ COMPATIBLE}$ or $[[G]]/RoHS [[Pb]]$

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2002/95/EC of the European Parliament and of the Council of 27 January 2003 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.







$$R_G = 25 \, \Omega$$

$$V_{DD} = 90 \, V, L = 5.88 \, mH$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I_{AS}^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$